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To: Assistant Commissioner for Patents

From: David Bonham
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Fax: 703-872-9318

Total pages: 10

Phone:

Date: 11/22/02

Re: In connection with prosecution in Serial. No.
09/881,254, please find enclosed a Response to
the Office Action mailed July 22, 2002.

CC:

Sincerely,

David Bonham

☐ Urgent ☐ For Review ☐ Please Comment ☐ Please Reply ☐ Please Recycle

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TECHNOLOGY CENTER 2800

Serial No. 09/881,254

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Fwu-Iuan Hshieh et al.

Serial No.: 09/881,254

Filed: 06/14/2001

Title: SYMMETRIC TRENCH MOSFET DEVICE AND METHOD OF MAKING SAME

Art Unit: 2826

Examiner: Mondt, Johannees P.

Docket No.: GS 134

VIA FACSIMILE 703-872-9318
Assistant Commissioner for Patents
Washington, D.C. 20231

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AMENDMENT AND RESPONSE

110.00 CH

Sir:

Responsive to the outstanding Office Action dated July 22, 2002 in the above-identified patent application, please enter the following amendments and remarks:

IN THE CLAIMS:

Please add new claims 25 and 26 as follows:

25. (Newly added) The trench MOSFET transistor device of claim 1, wherein said trench MOSFET transistor device comprises a plurality of source regions which are shorted to one another.

26. (Newly added) The trench MOSFET transistor device of claim 14, wherein said trench MOSFET transistor device comprises a plurality of source regions which are shorted to one another.